MC100EPT22

3.3V Dual LVTTL/LVCMOS to Differential LVPECL Translator

ON Semiconductor®

http://onsemi.com

Description

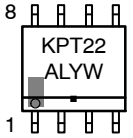
The MC100EPT22 is a dual LVTTL/LVCMOS to differential LVPECL translator. Because LVPECL (Positive ECL) levels are used only +3.3 V and ground are required. The small outline 8−lead package and the single gate of the EPT22 makes it ideal for those applications where space, performance, and low power are at a premium. Because the mature MOSAIC 5 process is used, low cost and high speed can be added to the list of features.

Features

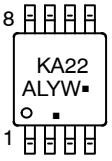
- 420 ps Typical Propagation Delay
- Maximum Frequency > 1.1 GHz Typical
- Operating Range: V_{CC} = 3.0 V to 3.6 V with GND = 0 V
- PNP LVTTL Inputs for Minimal Loading
- Q Output Will Default HIGH with Inputs Open
- The 100 Series Contains Temperature Compensation.
- Pb−Free Packages are Available

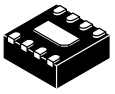
MARKING DIAGRAMS*

SOIC−8
D SUFFIX
CASE 751

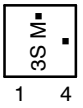


TSSOP−8
DT SUFFIX
CASE 948R





DFN8
MN SUFFIX
CASE 506AA



A	= Assembly Location
L	= Wafer Lot
Y	= Year
W	= Work Week
M	= Date Code
▪	= Pb−Free Package

(Note: Microdot may be in either location)

*For additional marking information, refer to Application Note AND8002/D.

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 6 of this data sheet.

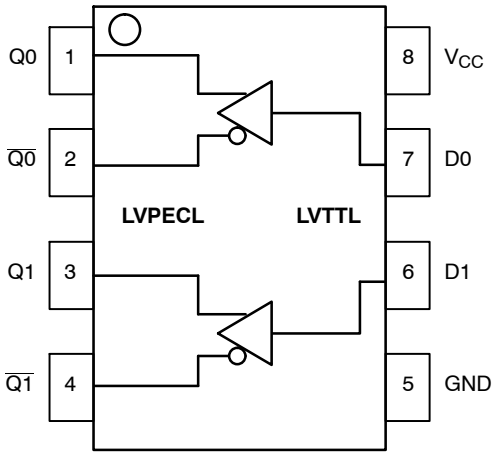


Figure 1. 8−Lead Pinout (Top View) **and Logic Diagram**

Table 1. PIN DESCRIPTION

PIN	FUNCTION
Q0, Q1, $\overline{Q0}$, $\overline{Q1}$	LVPECL Differential Outputs
D0, D1	LVTTL Inputs
V_{CC}	Positive Supply
GND	Ground
EP	(DFN8 only) Thermal exposed pad must be connected to a sufficient thermal conduit. Electrically connect to the most negative supply (GND) or leave unconnected, floating open.

Table 2. ATTRIBUTES

Characteristics		Value	
Internal Input Pulldown Resistor		N/A	
Internal Input Pullup Resistor		N/A	
ESD Protection	Human Body Model Machine Model Charged Device Model	> 4 kV > 200 V > 2 kV	
Moisture Sensitivity, Indefinite Time Out of Drypack (Note 1)		Pb Pkg	Pb−Free Pkg
	SOIC−8 TSSOP−8 DFN8	Level 1 Level 1 Level 1	Level 1 Level 3 Level 1
Flammability Rating	Oxygen Index: 28 to 34	UL 94 V−0 @ 0.125 in	
Transistor Count		164 Devices	
Meets or exceeds JEDEC Spec EIA/JESD78 IC Latchup Test			

1. For additional information, see Application Note AND8003/D.

Table 3. MAXIMUM RATINGS

Symbol	Parameter	Condition 1	Condition 2	Rating	Unit
V_{CC}	Power Supply	GND = 0 V		6	V
V_I	Input Voltage	GND = 0 V	$V_I \le V_{CC}$	6 to 0	V
I_{out}	Output Current	Continuous Surge		50 100	mA mA
T_A	Operating Temperature Range			−40 to +85	°C
T_{stg}	Storage Temperature Range			−65 to +150	°C
θ_{JA}	Thermal Resistance (Junction−to−Ambient)	0 lfpm 500 lfpm	SOIC−8 SOIC−8	190 130	°C/W °C/W
θ_{JC}	Thermal Resistance (Junction−to−Case)	Standard Board	SOIC−8	41 to 44	°C/W
θ_{JA}	Thermal Resistance (Junction−to−Ambient)	0 lfpm 500 lfpm	TSSOP−8 TSSOP−8	185 140	°C/W °C/W
θ_{JC}	Thermal Resistance (Junction−to−Case)	Standard Board	TSSOP−8	41 to 44	°C/W
θ_{JA}	Thermal Resistance (Junction−to−Ambient)	0 lfpm 500 lfpm	DFN8 DFN8	129 84	°C/W °C/W
T_{sol}	Wave Solder Pb Pb−Free			265 265	°C
θ_{JC}	Thermal Resistance (Junction−to−Case)	(Note 2)	DFN8	35 to 40	°C/W

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

2. JEDEC standard multilayer board − 2S2P (2 signal, 2 power)

Table 4. TTL INPUT DC CHARACTERISTICS V_{CC} = 3.3 V, GND = 0 V, T_A= −40°C to 85°C

Symbol	Characteristic	Condition	Min	Typ	Max	Unit
I_{IH}	Input HIGH Current	V_{IN} = 2.7 V			20	μA
I_{IHH}	Input HIGH Current MAX	$V_{IN} = V_{CC}$			100	μA
I_{IL}	Input LOW Current	V_{IN} = 0.5 V			−0.6	mA
V_{IK}	Input Clamp Voltage	I_{IN} = −18 mA			−1.0	V
V_{IH}	Input HIGH Voltage		2.0			V
V_{IL}	Input LOW Voltage				0.8	V

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm. Electrical parameters are guaranteed only over the declared operating temperature range. Functional operation of the device exceeding these conditions is not implied. Device specification limit values are applied individually under normal operating conditions and not valid simultaneously.

Table 5. PECL OUTPUT DC CHARACTERISTICS V_{CC} = 3.3 V, GND = 0.0 V (Note 3)

		−40°C			25°C			85°C			
Symbol	Characteristic	Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	Unit
I_{CC}	Power Supply Current	32	43	55	35	45	60	37	46	62	mA
V_{OH}	Output HIGH Voltage (Note 4)	2155	2280	2405	2155	2280	2405	2155	2280	2405	mV
V_{OL}	Output LOW Voltage (Note 4)	1355	1480	1605	1355	1480	1605	1355	1480	1605	mV

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm. Electrical parameters are guaranteed only over the declared operating temperature range. Functional operation of the device exceeding these conditions is not implied. Device specification limit values are applied individually under normal operating conditions and not valid simultaneously.

3. Output parameters vary 1:1 with V_{CC}.
4. All loading with 50 Ω to V_{CC} − 2.0 V.

Table 6. AC CHARACTERISTICS V_{CC} = 3.0 V to 3.6 V, GND = 0.0 V (Note 5)

		–40°C			25°C			85°C			
Symbol	**Characteristic**	**Min**	**Typ**	**Max**	**Min**	**Typ**	**Max**	**Min**	**Typ**	**Max**	**Unit**
f_{max}	Maximum Frequency (Figure 2)	0.8	1.1		0.8	1.1		0.8	1.1		GHz
t_{PLH}, t_{PHL}	Propagation Delay to Output Differential	250	400	650	250	420	675	300	500	700	ps
t_{skew}	Within–Device Skew (Note 6) Device–to–Device Skew (Note 7)		50 200	100 400		50 200	100 425		50 200	100 400	ps
t_{JITTER}	Random Clock Jitter (Figure 2)		0.2	< 1		0.2	< 1		0.2	< 1	ps
$t_{JIT(\Phi)}$	Additive Phase RMS Jitter Integration Range 12 kHz to 20 MHz 25 MHz 156.25 MHz					 0.05 0.16					ps
t_r t_f	Output Rise/Fall Times Q, $\overline{Q}$ (20% – 80%)	50	110	200	60	120	220	70	140	250	ps

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm. Electrical parameters are guaranteed only over the declared operating temperature range. Functional operation of the device exceeding these conditions is not implied. Device specification limit values are applied individually under normal operating conditions and not valid simultaneously.

5. Measured using a 2.4 V source, 50% duty cycle clock source. All loading with 50 Ω to V_{CC} – 2.0 V.
6. Skew is measured between outputs under identical transitions and conditions on any one device.
7. Device–to–Device Skew for identical transitions at identical V_{CC} levels.

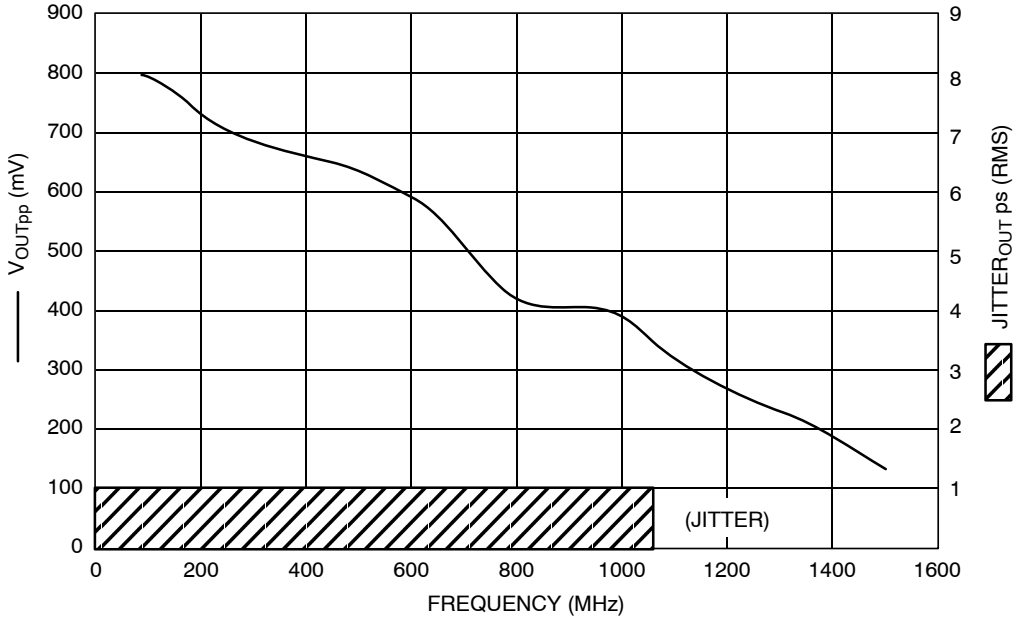


Figure 2. F_{max}/Jitter

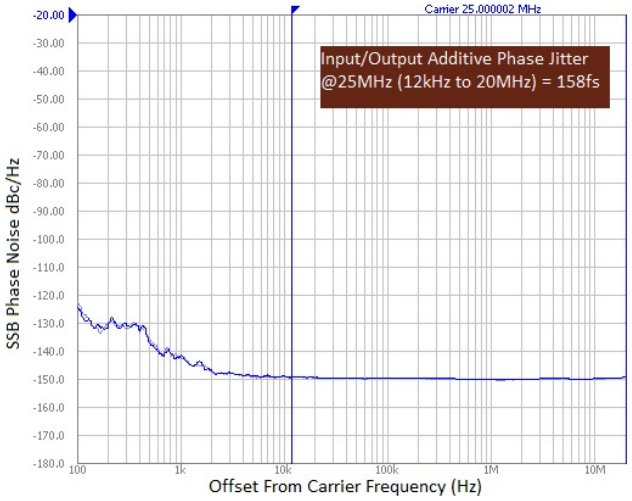


Figure 3. Typical Phase Noise Plot at $f_{carrier}$ = 25 MHz

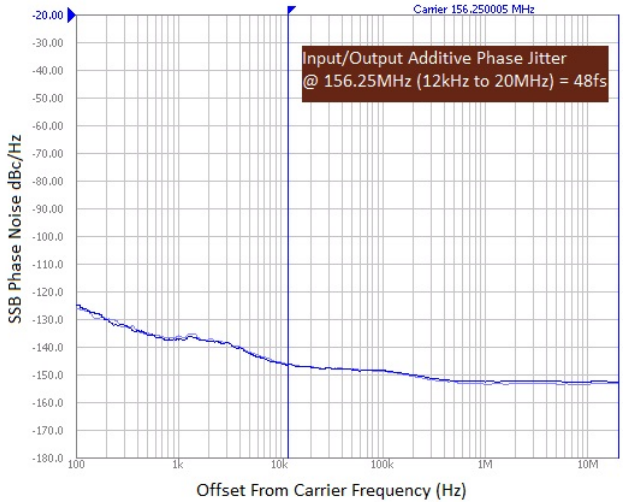


Figure 4. Typical Phase Noise Plot at $f_{carrier}$ = 156.25 MHz

The above phase noise plots captured using Agilent E5052A show additive phase noise of the MC100EPT22 device at frequencies 25 MHz and 156.25 MHz respectively at an operating voltage of 3.3 V in room temperature. The RMS Phase Jitter contributed by the device (integrated between 12 kHz and 20 MHz; as shown in the shaded region of the plot) at each of the frequencies is 158 fs and 48 fs respectively. The input source used for the phase noise measurements is Agilent E8663B.

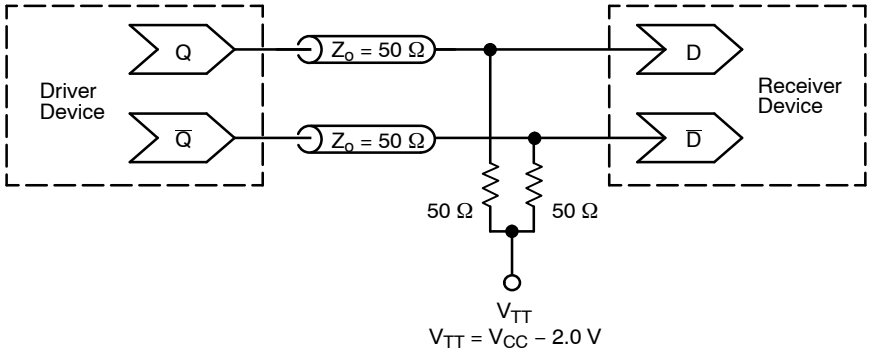


Figure 5. Typical Termination for Output Driver and Device Evaluation (See Application Note AND8020/D – Termination of ECL Logic Devices.)

ORDERING INFORMATION

Device	Package	Shipping†
MC100EPT22D	SOIC−8	98 Units / Rail
MC100EPT22DG	SOIC−8 (Pb−Free)	98 Units / Rail
MC100EPT22DR2	SOIC−8	2500 / Tape & Reel
MC100EPT22DR2G	SOIC−8 (Pb−Free)	2500 / Tape & Reel
MC100EPT22DT	TSSOP−8	100 Units / Rail
MC100EPT22DTG	TSSOP−8 (Pb−Free)	100 Units / Rail
MC100EPT22DTR2	TSSOP−8	2500 / Tape & Reel
MC100EPT22DTR2G	TSSOP−8 (Pb−Free)	2500 / Tape & Reel
MC100EPT22MNR4G	DFN8 (Pb−Free)	1000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Resource Reference of Application Notes

AN1405/D – ECL Clock Distribution Techniques

AN1406/D – Designing with PECL (ECL at +5.0 V)

AN1503/D – ECLinPS™ I/O SPiCE Modeling Kit

AN1504/D – Metastability and the ECLinPS Family

AN1568/D – Interfacing Between LVDS and ECL

AN1672/D – The ECL Translator Guide

AND8001/D – Odd Number Counters Design

AND8002/D – Marking and Date Codes

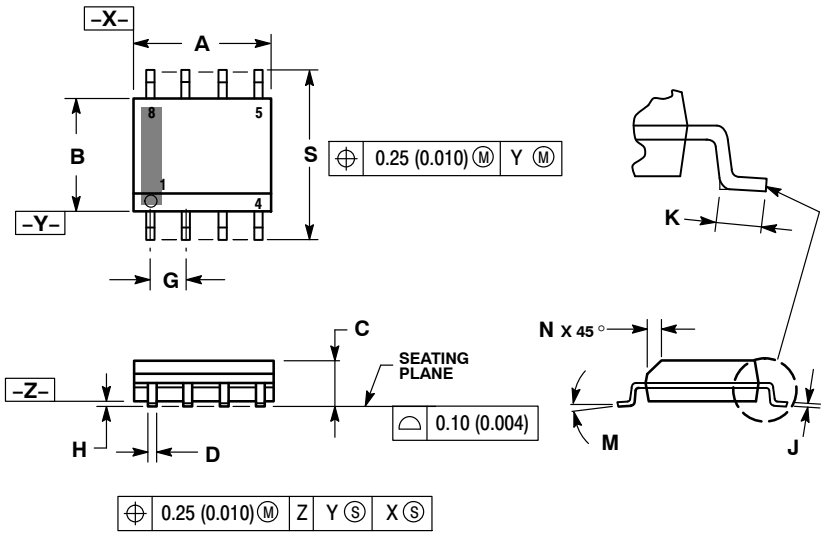
AND8020/D – Termination of ECL Logic Devices

AND8066/D – Interfacing with ECLinPS

AND8090/D – AC Characteristics of ECL Devices

PACKAGE DIMENSIONS

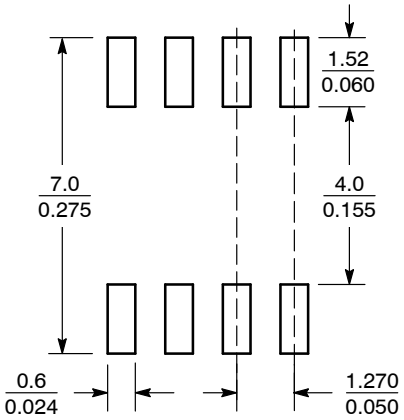
SOIC−8 NB
CASE 751−07
ISSUE AK



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. 751−01 THRU 751−06 ARE OBSOLETE. NEW STANDARD IS 751−07.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	4.80	5.00	0.189	0.197
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.053	0.069
D	0.33	0.51	0.013	0.020
G	1.27 BSC		0.050 BSC	
H	0.10	0.25	0.004	0.010
J	0.19	0.25	0.007	0.010
K	0.40	1.27	0.016	0.050
M	0°	8°	0°	8°
N	0.25	0.50	0.010	0.020
S	5.80	6.20	0.228	0.244

SOLDERING FOOTPRINT*

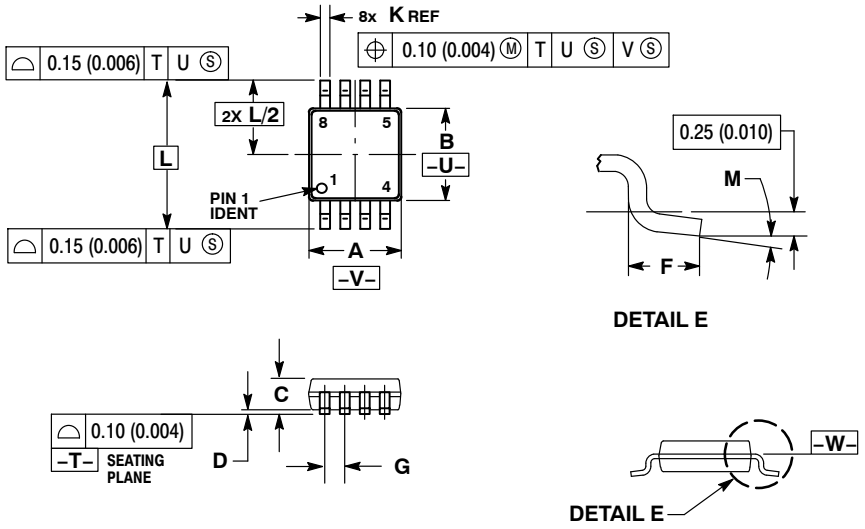


SCALE 6:1 $\left(\frac{\text{mm}}{\text{inches}}\right)$

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

TSSOP−8
DT SUFFIX
CASE 948R−02
ISSUE A

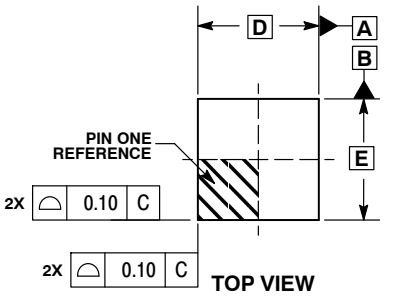


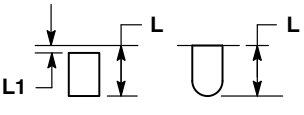
NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH. PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
6. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE −W−.

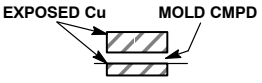
	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	2.90	3.10	0.114	0.122
B	2.90	3.10	0.114	0.122
C	0.80	1.10	0.031	0.043
D	0.05	0.15	0.002	0.006
F	0.40	0.70	0.016	0.028
G	0.65 BSC		0.026 BSC	
K	0.25	0.40	0.010	0.016
L	4.90 BSC		0.193 BSC	
M	0°	6°	0°	6°

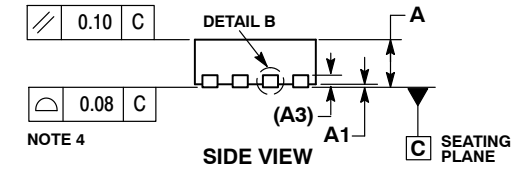
PACKAGE DIMENSIONS

DFN8 2x2, 0.5P
CASE 506AA
ISSUE E



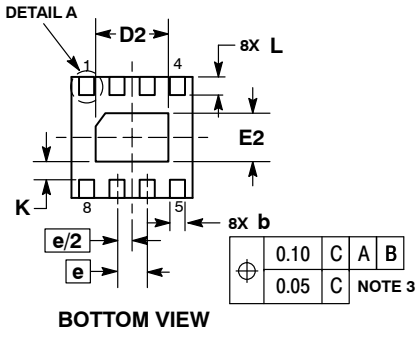




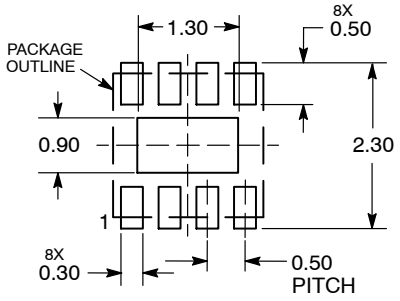


NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994 .
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.20 MM FROM TERMINAL TIP.
4. COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.

	MILLIMETERS	
DIM	MIN	MAX
A	0.80	1.00
A1	0.00	0.05
A3	0.20 REF	
b	0.20	0.30
D	2.00 BSC	
D2	1.10	1.30
E	2.00 BSC	
E2	0.70	0.90
e	0.50 BSC	
K	0.30 REF	
L	0.25	0.35
L1	---	0.10



RECOMMENDED SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

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